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RFL2N05, RFL2N06

2A, 50V and 60V, 0.95 Ohm, N-Channel Power MOSFETs

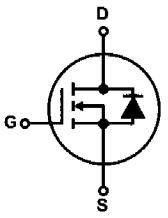
Features

- **2A, 50V and 60V**
- **$r_{DS(ON)} = 0.95\Omega$**
- **SOA is Power-Dissipation Limited**
- **Nanosecond Switching Speeds**
- **Linear Transfer Characteristics**
- **High Input Impedance**
- **Majority Carrier Device**
- **Related Literature**

Description

These are N-Channel enhancement mode silicon gate power field effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Symbol



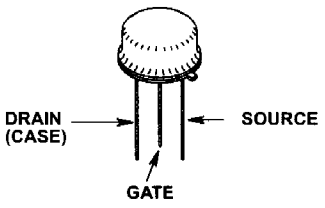
Ordering Information

PART NUMBER	PACKAGE	BRAND
RFL2N05	TO-205AF	RFL2N05
RFL2N05	TO-205AF	RFL2N05

NOTE: When ordering, include the entire part number.

Packaging

JEDEC TO-205AF



Absolute Maximum Ratings $T_C = 25^oC$, Unless Otherwise Specified

		RFL2N05	RLF2N06	UNITS
Drain to Source Voltage (Note 1)	V_{DSS}	50	60	V
Drain to Gate Voltage (R_{GS} = 1MΩ) (Note 1)	V_{DGR}	50	60	V
Gate to Source Voltage	V_{GS}	±20	±20	V
Drain Current, RMS Continuous	I_D	2	2	A
Pulsed	I_{DM}	10	10	A
Maximum Power Dissipation	P_D	8.33	8.33	W
Linear Derating Factor		0.0667	0.0667	W/ ^{o}C
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	^{o}C
Maximum Temperature for Soldering				
Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	300	^{o}C
Package Body for 10s, See Techbrief 334	T_{pkg}	260	260	^{o}C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. $T_J = 25^oC$ to 125^oC.

Electrical Specifications $T_C = 25^oC$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	I_D = 250µA, V_{GS} = 0				
RFL2N05			50	-	-	V
RFL2N06			60	-	-	V
Gate to Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, I_D = 250µA, (Figure 8)	2	-	4	V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} = 0.8 x Rated BV_{DSS}, $T_C = 25^oC$	-	-	1	µA
		$T_C = 125^oC$	-	-	25	µA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0	-	-	±100	nA
Drain to Source On Voltage (Note 2)	$V_{DS(ON)}$	I_D = 1A, V_{GS} = 10V	-	-	0.95	V
		I_D = 2A, V_{GS} = 10V	-	-	2.0	V
		I_D = 4A, V_{GS} = 15V	-	-	4.8	V
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	I_D = 1A, V_{GS} = 10V, (Figures 6, 7)	-	-	0.95	Ω
Forward Transconductance (Note 2)	g_{fs}	I_D = 1A, V_{DS} = 10V, (Figure 10)	400	-	-	S
Turn-On Delay Time	$t_{d(ON)}$	I_D = 1A, V_{DD} = 30V, R_{GS} = 50Ω, V_{GS} = 10V, (Figures 11, 12, 13)	-	6	15	ns
Rise Time	t_r		-	14	30	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	16	30	ns
Fall Time	t_f		-	30	50	ns
Input Capacitance	C_{ISS}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz, (Figure 9)	-	-	200	pF
Output Capacitance	C_{OSS}		-	-	85	pF
Reverse-Transfer Capacitance	C_{RSS}		-	-	30	pF
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	15	^{o}C/W

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage (Note 2)	V_{SD}	I_{SD} = 1A	-	-	1.4	V
Diode Reverse Recovery Time	t_{rr}	I_{SD} = 2A, dI_{SD}/dt = 50A/µs	-	100	-	ns

NOTE:

2. Pulse test: pulse width ≤ 300µs, duty cycle ≤ 2%.